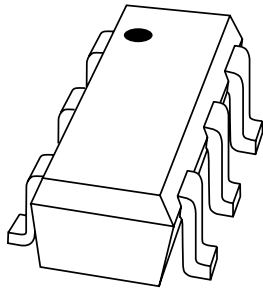


# DATA SHEET



## **PBSS2515YPN**

15 V low  $V_{CE(sat)}$  NPN/PNP  
transistor

Product data sheet  
Supersedes data of 2002 May 08

2005 Jan 11

# 15 V low $V_{CE(sat)}$ NPN/PNP transistor

# PBSS2515YPN

### FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Replaces two SC-70 packaged low  $V_{CEsat}$  transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

### APPLICATION

- General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

### DESCRIPTION

NPN/PNP low  $V_{CEsat}$  transistor pair in a SC-88 plastic package.

### MARKING

TYPE NUMBER	MARKING CODE
PBSS2515YPN	N8*

### Note

- \* = -: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China.

### ORDERING INFORMATION

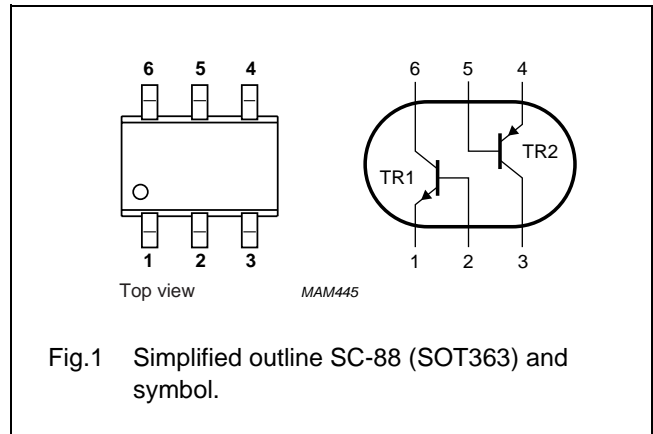
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS2515YPN	SC-88	plastic surface mounted package; 6 leads	SOT363

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	15	V
$I_{CM}$	peak collector current	1	A
$R_{CEsat}$	equivalent on-resistance	<500	$m\Omega$

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



15 V low  $V_{CE(sat)}$  NPN/PNP transistor

## PBSS2515YPN

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor; for the PNP transistor with negative polarity</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	15	V
$V_{CEO}$	collector-emitter voltage	open base	–	15	V
$V_{EBO}$	emitter-base voltage	open collector	–	6	V
$I_C$	collector current (DC)		–	500	mA
$I_{CM}$	peak collector current		–	1	A
$I_{BM}$	peak base current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	200	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	416	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

15 V low  $V_{CE(sat)}$  NPN/PNP transistor

## PBSS2515YPN

**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

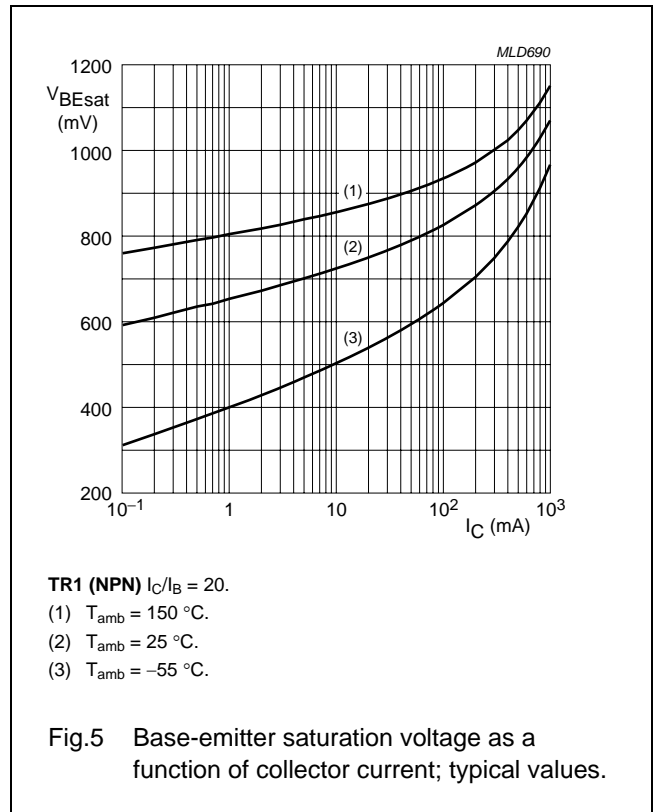
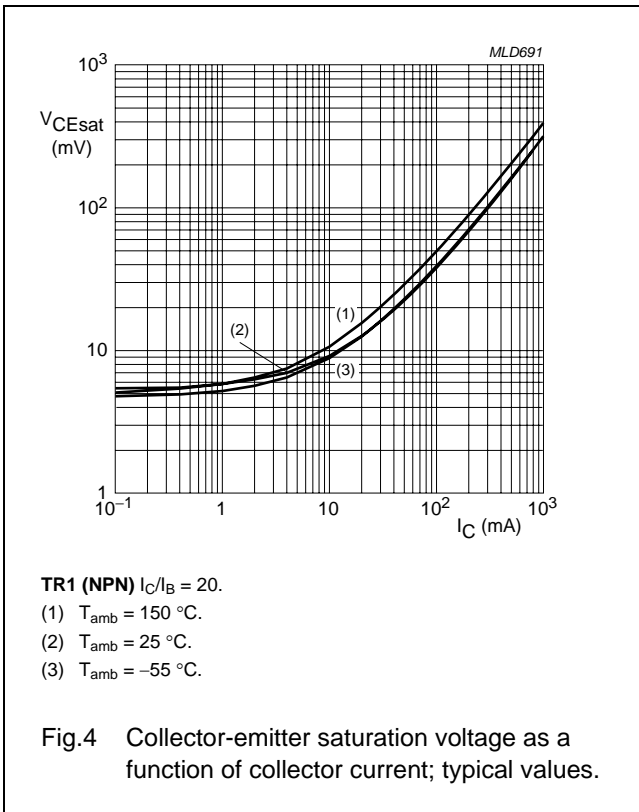
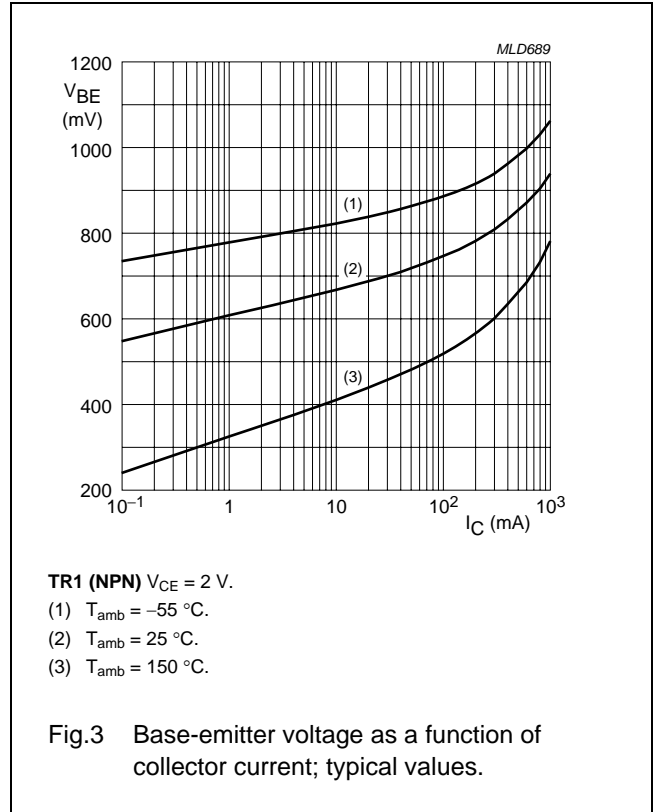
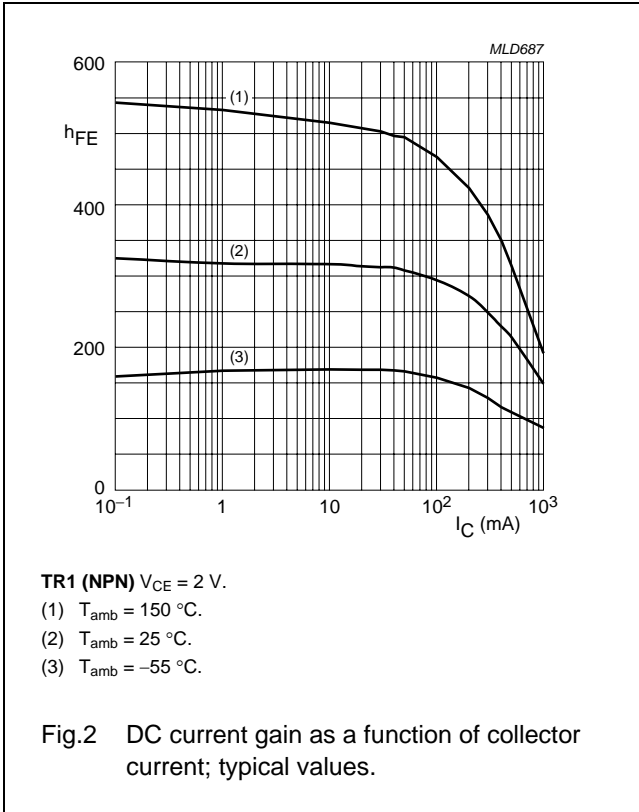
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor; for the PNP transistor with negative polarity</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 15\text{ V}; I_E = 0\text{ A}$	–	–	100	nA
		$V_{CB} = 15\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	–	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 10\text{ mA}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	150	–	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}; \text{note 1}$	90	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	25	mV
		$I_C = 200\text{ mA}; I_B = 10\text{ mA}$	–	–	150	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	250	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	300	<500	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	–	–	0.9	V
<b>NPN transistor</b>						
$f_T$	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	250	420	–	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	–	4.4	6	pF
<b>PNP transistor</b>						
$f_T$	transition frequency	$I_C = -100\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	100	280	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	–	–	10	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

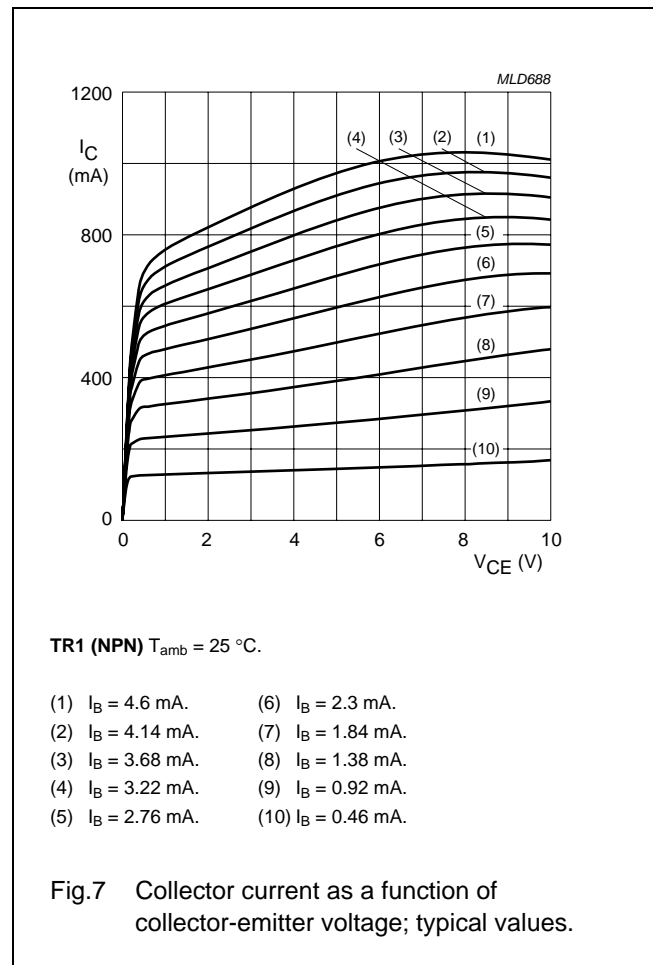
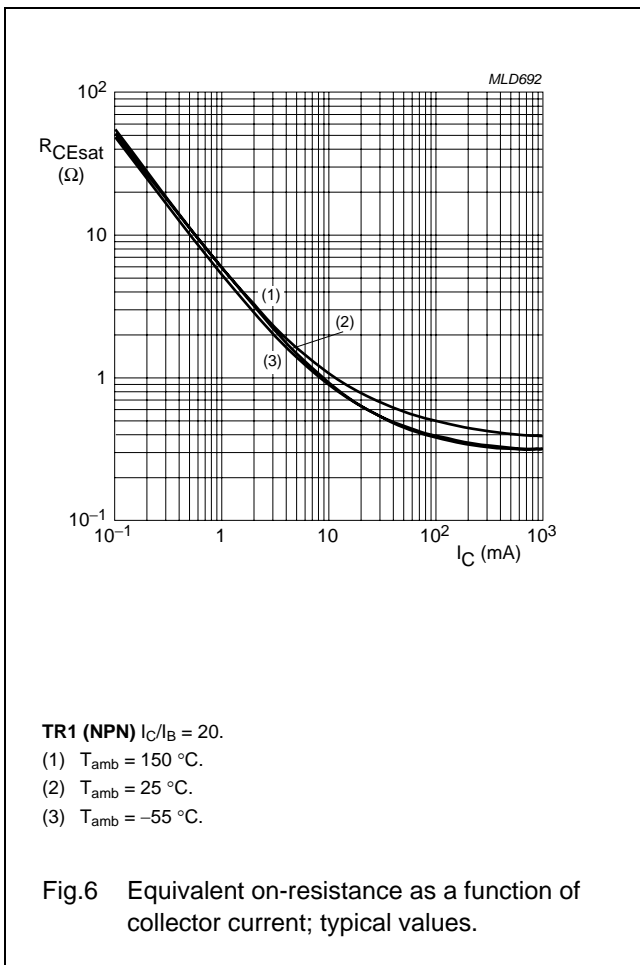
15 V low  $V_{CE(sat)}$  NPN/PNP transistor

PBSS2515YPN



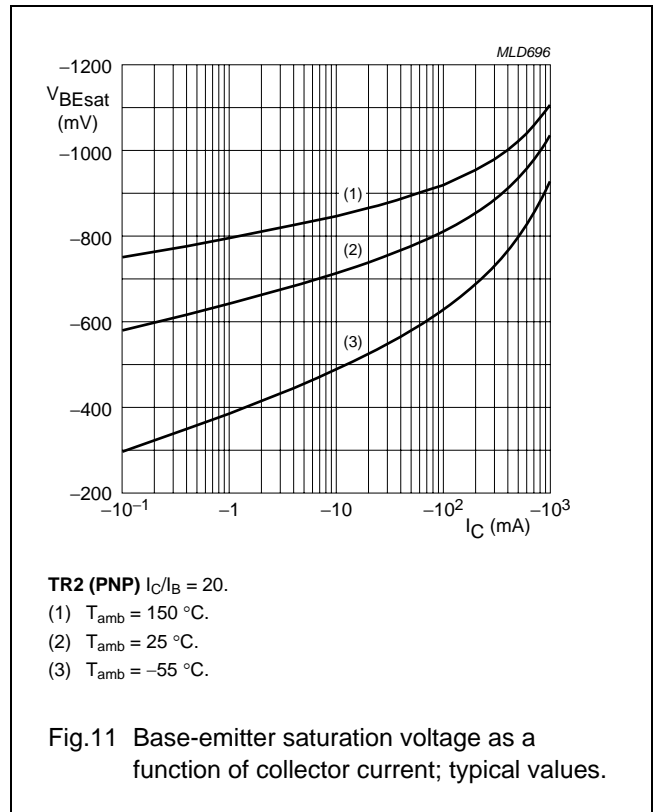
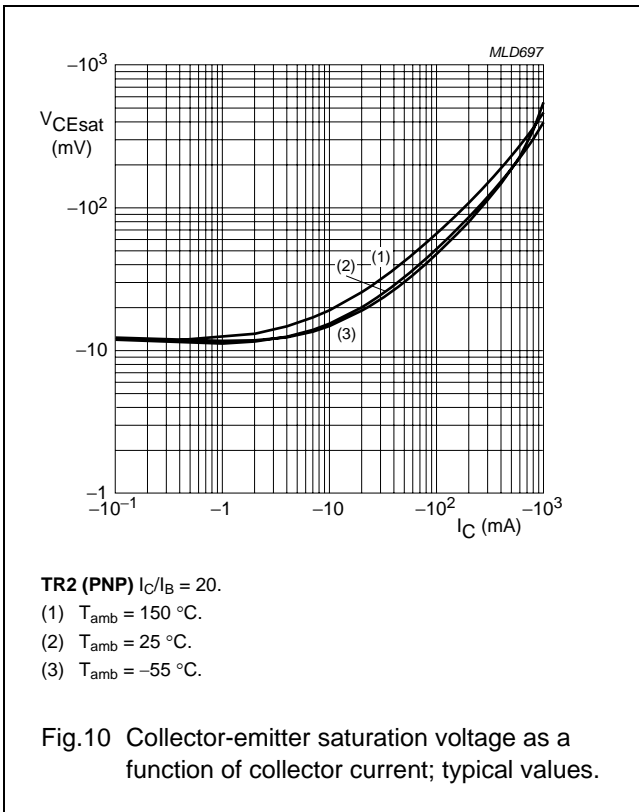
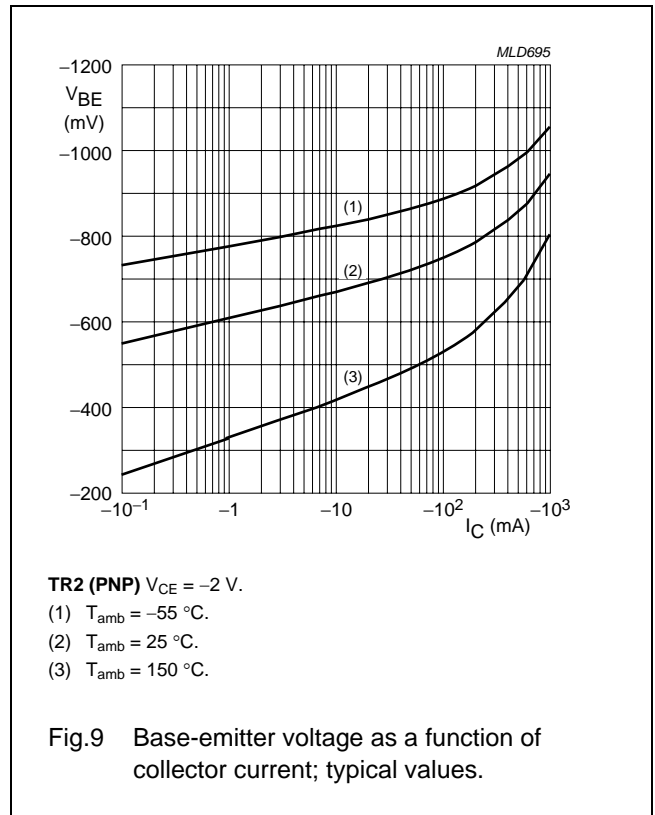
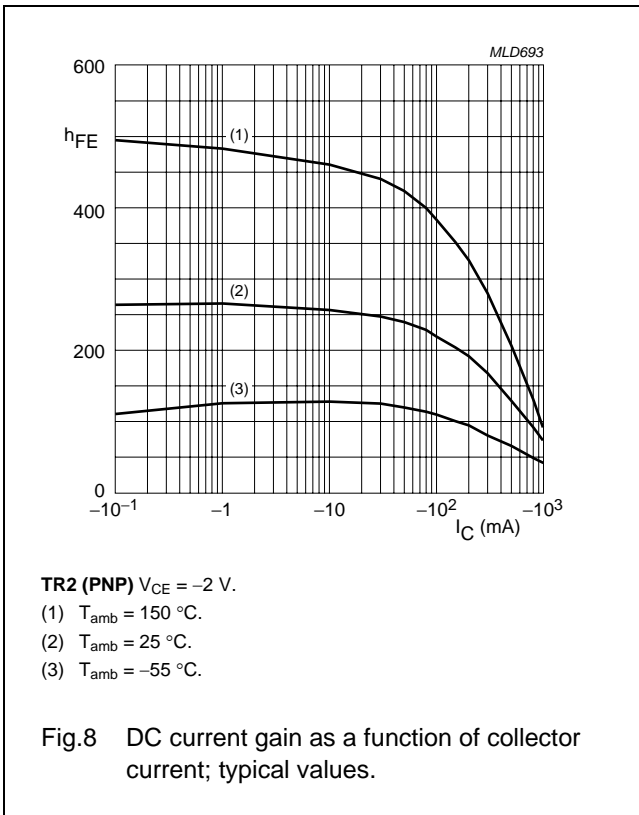
15 V low  $V_{CE(sat)}$  NPN/PNP transistor

PBSS2515YPN



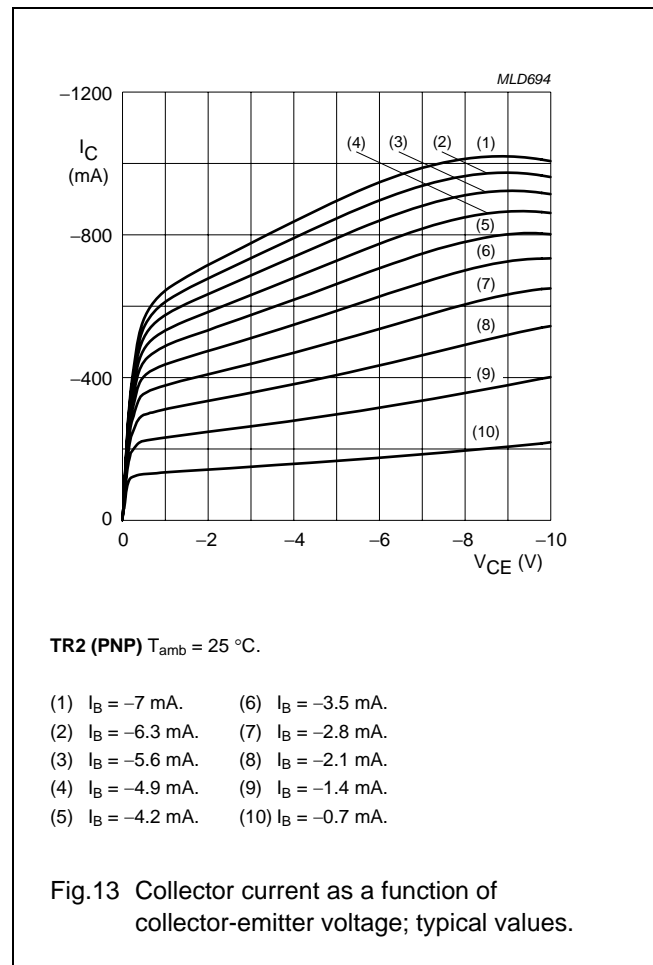
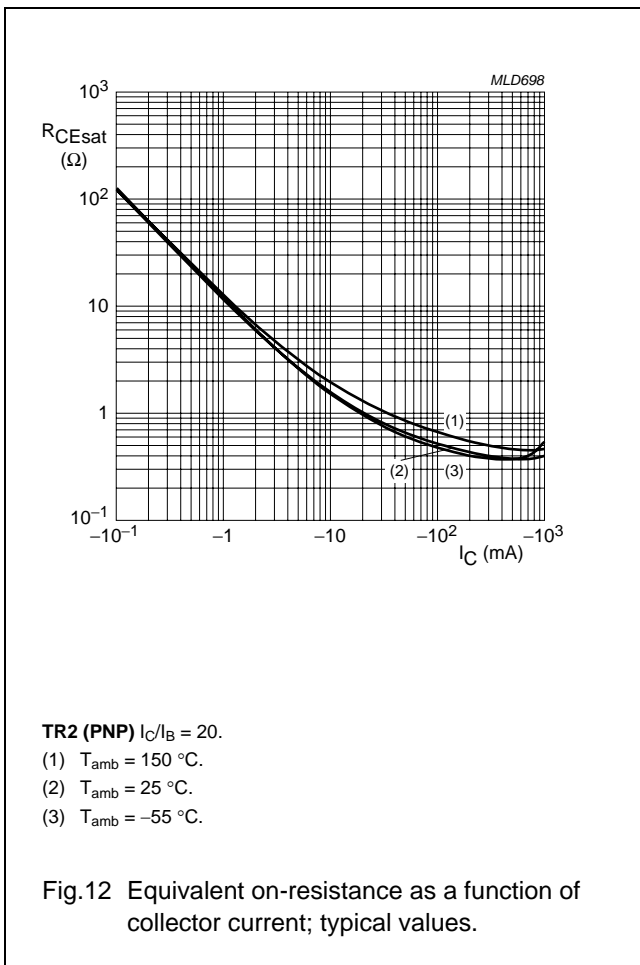
15 V low  $V_{CE(sat)}$  NPN/PNP transistor

PBSS2515YPN



15 V low  $V_{CE(sat)}$  NPN/PNP transistor

PBSS2515YPN





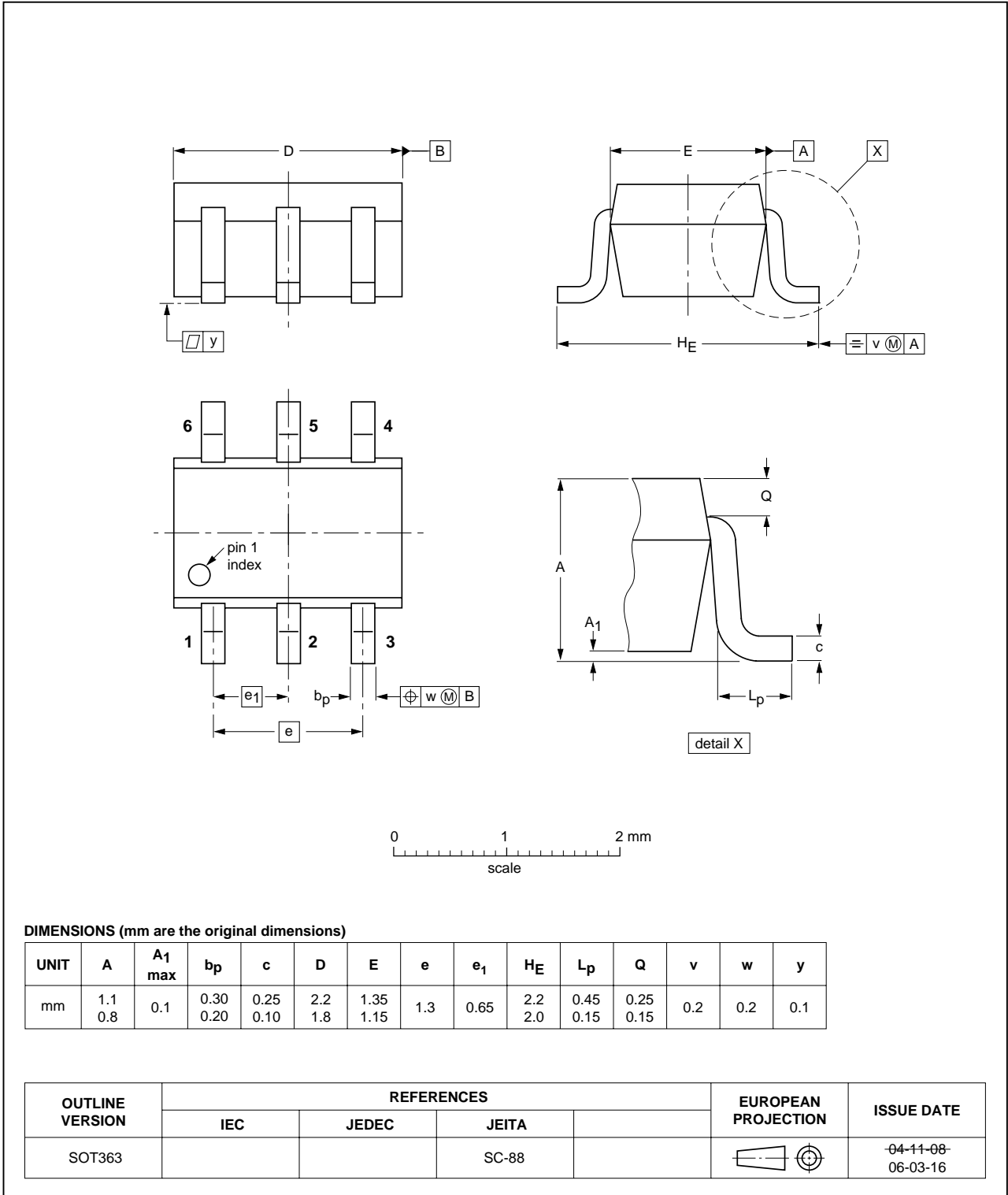
15 V low  $V_{CE(sat)}$  NPN/PNP transistor

PBSS2515YPN

PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads

SOT363



15 V low  $V_{CE(sat)}$  NPN/PNP transistor

PBSS2515YPN

**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Contact information**

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